# Thermally-Enhanced High Power RF GaN on SiC HEMT 400 W, 50 V, 960 – 1215 MHz

# **Description**

The GTVA104001FA is a 400-watt GaN on SiC high electron mobility transistor (HEMT) for use in the 960 to 1215 MHz frequecy band. It features input matching, high efficiency, and a thermally-enhanced surface-mount package with earless flange.

#### **Features**

- GaN on SiC HEMT technology
- · Broadband internal input matching
- Typical Pulsed CW performance, 960 1215 MHz, 50V,
  - Output power = 410 W
  - Drain Efficiency = 70 %
  - Gain = 19 dB
  - Pulse width =  $128 \mu s$
  - Duty cycle = 10 %
- · Pb-free and RoHS compliant

Advance Specification Data Sheets describe products that are being considered by Wolfspeed for development and market introduction. The target performance shown in Advance Specifications is not final and should not be used for any design activity. Please contact Wolfspeed about the future availability of these products.



GTVA104001FA Package H-37265J-2

# **Target RF Characteristics**

Typical RF Performance (tested in Wolfspeed test fixture)

 $V_{DD} = 50 \text{ V}$ ,  $I_{DQ} = 50 \text{ mA}$ ,  $P_{OUT} = 400 \text{ W}$ , f = 960 - 1215 MHz, Pulse Width = 128 µs, 10% duty cycle

Characteristic	Symbol	Min	Тур	Max	Unit
Linear Gain	G <sub>ps</sub>	_	19	_	dB
Drain Efficiency	$\eta_{D}$	_	70	_	%

All published data at  $T_{CASE} = 25^{\circ}C$  unless otherwise indicated

ESD: Electrostatic discharge sensitive device—observe handling precautions!

## **DC Characteristics**

Characteristic	Conditions	Symbol	Min	Тур	Max	Unit
Drain-source Breakdown Voltage	$V_{GS} = -8 \text{ V}, I_D = 10 \text{ mA}$	V <sub>(BR)DSS</sub>	150	_	_	V
Gate Threshold Voltage	$V_{DS} = 10 \text{ V}, I_{D} = 42 \text{ mA}$	V <sub>GS(th)</sub>	-6	-3	-2.2	V

# **Recommended Operating Conditions**

Parameter	Conditions	Symbol	Min	Тур	Max	Unit
Drain Operating Voltage		$V_{DD}$	0	_	50	V
Gate Quiescent Voltage	$V_{DS} = 50 \text{ V}, I_D = 100 \text{ mA}$	$V_{GS(Q)}$	_	-3.2	_	V

# **Absolute Maximum Ratings**

Parameter	Symbol	Value	Unit
Drain-source Voltage	V <sub>DSS</sub>	125	V
Gate-source Voltage	$V_{GS}$	-10 to +2	V
Gate Current	$I_{G}$	38	mA
Drain Current	I <sub>D</sub>	5	Α
Junction Temperature	TJ	225	°C
Storage Temperature Range	T <sub>STG</sub>	-65 to +150	°C

Operation above the maximum values listed here may cause permanent damage. Maximum ratings are absolute ratings; exceeding only one of these values may cause irreversible damage to the component. Exposure to absolute maximum rating conditions for extended periods may affect device reliability. For reliable continuous operation, the device should be operated within the operating voltage range  $(V_{DD})$  specified above.

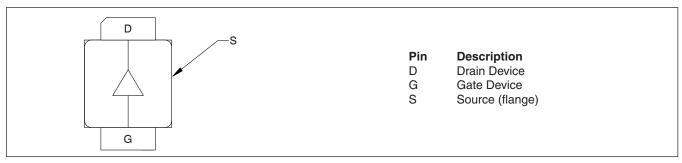
#### **Thermal Chracteristics**

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction to Case ( $f = 1030 \text{ MHz}$ , $V_{DD} = 50 \text{ V}$ ,	$R_{\thetaJC}$	0.13	°C/W
$I_{GS}$ = 100 mA, $T_F$ = 70 °C, $P_{OUT}$ = 400 W, Pulse Width = 128 $\mu s,$			
10% duty cycle)			

# **Ordering Information**

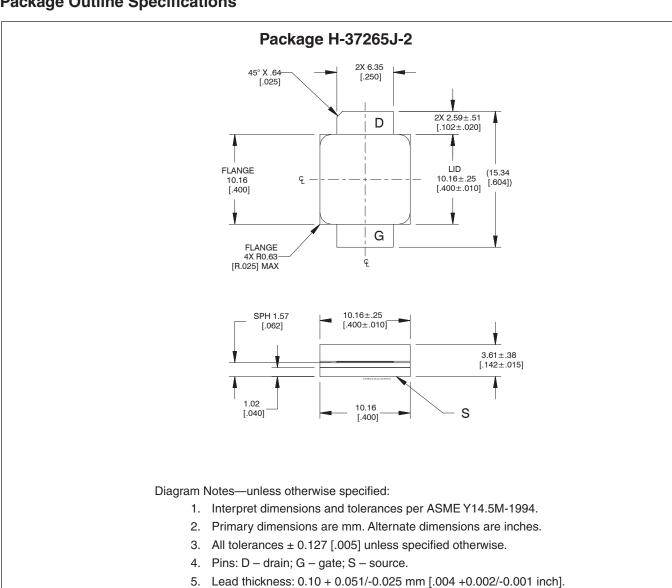
Type and Version	Order Code	Package	Shipping
GTVA104001FA V1 R0	TBD	H-37265J-2, earless flange	Tape & Reel, 50 pcs
GTVA104001FA V1 R2	TBD	H-37265J-2, earless flange	Tape & Reel, 250 pcs

## Pinout Diagram (top view)



Lead connections for GTVA104001FA

# **Package Outline Specifications**



6. Gold plating thickness:  $1.14 \pm 0.38$  micron [45  $\pm$  15 microinch].

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#### **Revision History**

Revision	Date	Data Sheet Type	Page	Subjects (major changes since last revision)
01	2016-05-03	Advance	All	Data Sheet reflects advance specification for product development
02	2016-05-08	Advance	All	Converted to Wolfspeed Data Sheet, updated DC and thermal characteristics

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#### Notes

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